Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-340-0685

	osure Material:
Meta	
	rall Length:
	veen 0.165 inches and 0.185 inches
	ninal Length:
	0 inches
• • • •	rall Diameter:
	veen 0.335 inches and 0.370 inches
	t Electronic Device Engineering Council/jedec/case Outline Designation:
To-7	-
	ponent Name And Quantity:
	nsistor
	nting Method:
Term	
	ninal Circle Diameter:
	0 inches
Feat	ures Provided:
Hern	netically sealed case
Sem	iconductor Material:
Silico	on all transistor
Volta	age Rating In Volts Per Characteristic:
5.0	collector to emitter voltage, dc all transistor
Curr	ent Rating Per Characteristic:
100.	00 microamperes source cutoff current all transistor
Pow	er Rating Per Characteristic:
750.	0 milliwatts small-signal input power, common-collector absolute all transistor
Tran	sfer Ratio:
200.	0 static forward current transfer ratio, common-emitter all transistor
Spee	cial Features:
All tr	ansistor junction pattern arrangement: npn
Tern	ninal Type And Quantity:
8 un	insulated wire lead
Spee	cification Data:
2848	30-1854-1046 manufacturers specification control
Shel	f Life:
N/a	
Unit	Of Measure:
Dem	ilitarization:
No	
Fiig:	
A11(	Da0